Elektronische Bauelemente

BC846S

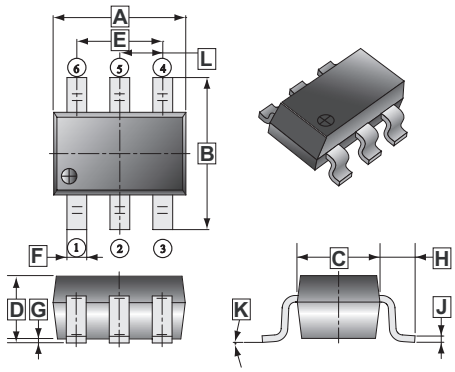
Plastic-Encapsulate
Multi-Chip (NPN+NPN) Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

SOT-363



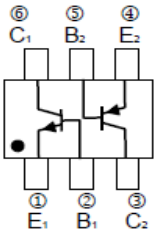
MARKING :

4Ft

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-363	3K	7 inch

Top View



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	G	0.100 REF.	
B	2.15	2.45	H	0.525 REF.	
C	1.15	1.35	J	0.08	0.15
D	0.90	1.10	K	8°	
E	1.20	1.40	L	0.650 TYP.	
F	0.15	0.35			

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	80	V
Collector-Emitter Voltage	$V_{(BR)CEO}$	65	V
Emitter-Base Voltage	$V_{(BR)EBO}$	6	V
Collector Current	I_C	0.1	A
Collector Power Dissipation	P_C	200	mW
Junction & Storage Temperature	T_J, T_{STG}	150, -65~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	-	-	V	I_C=10μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	65	-	-		I_C=10mA , I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	-	-		I_E=10μA , I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	15	nA	V_{CB}= 30V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	5	μA	V_{EB}=5V, I_C=0
DC Current Gain	h_{FE}	110	-	-		V_{CE}=5V, I_C=2mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-	-	0.1	V	I_C=10mA, I_B=0.5mA
	$V_{CE(sat)}$	-	-	0.3	V	I_C=100mA, I_B=5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-	0.77	-	V	I_C=10mA, I_B=0.5mA
Transition Frequency	f_T	100	-	-	MHz	V_{CB}=5V, I_E=10mA, f=100MHz
Collector Output Capacitance	C_{ob}	-	-	1.5	pF	V_{CB}=10V, I_E=0, f=1MHz